

- Preface p. xi
- 1 Background on Microwave Transistors p. 1
- 1.1 Introduction p. 1
- 1.2 Microwave Transistor Figures of Merit p. 4
- 1.2.1 The Concept of Two-Port Networks p. 4
- 1.2.2 The Problem of Stability p. 6
- 1.2.3 Power Gain Definitions p. 7
- 1.2.4 The Characteristic Frequencies f_T and f_{max} p. 9
- 1.2.5 Minimum Noise Figure and Associated Gain p. 11
- 1.2.6 Output Power and Power-Added Efficiency p. 12
- 1.3 Historical View of Microwave Transistors p. 12
- 1.3.1 The Early Years p. 12
- 1.3.2 Development of Microwave Transistors with Heterostructures p. 15
- 1.3.3 Recent Developments p. 20
- 1.4 State of the Art of Microwave Transistors in the Year 2001 p. 21
- 1.4.1 III-V FETs p. 21
- 1.4.2 BJTs and HBTs p. 28
- 1.4.3 Wide Bandgap Transistors p. 34
- 1.4.4 Si MOSFETs p. 37
- 1.5 Application Aspects p. 38
- 1.5.1 Civil Applications of Microwave Systems p. 38
- 1.5.2 Other Applications of Transistors with GHz Capabilities p. 40
- 1.5.3 Microwave Transistors for Wireless Communications up to 2.5 GHz p. 41
- 1.6 Summary and Outlook p. 43
- References p. 52
- 2 Basic Semiconductor Physics p. 61
- 2.1 Introduction p. 61
- 2.2 Free-Carrier Densities p. 63
- 2.2.1 Band Diagrams and Band Structure p. 63
- 2.2.2 Carrier Statistics p. 67
- 2.2.3 Approximations for the Carrier Densities p. 69
- 2.3 Carrier Transport p. 77
- 2.3.1 Introduction p. 77
- 2.3.2 Classical Description of Carrier Transport p. 78
- 2.3.3 Nonclassical Description of Carrier Transport p. 91
- 2.4 PN Junctions p. 96
- 2.5 Schottky Junctions p. 106
- 2.6 Impact Ionization p. 108
- 2.7 Self-Heating p. 112
- References p. 117
- 3 Heterostructure Physics p. 121
- 3.1 Introduction p. 121
- 3.2 Band Diagrams p. 125
- 3.2.1 The Anderson Model p. 125
- 3.2.2 Built-In Voltage and Thickness of the Space-Charge Region p. 127
- 3.2.3 Bandgaps and Band Offsets p. 130

- 3.3 Carrier Transport Across Heterojunctions p. 134
- 3.3.1 Currents Across Spike Heterojunctions p. 134
- 3.3.2 Currents Across Smooth Heterojunctions p. 139
- 3.4 Carrier Transport Parallel to Heterojunctions and Two-Dimensional Electron Gas p. 140
- 3.4.1 Band Diagram p. 140
- 3.4.2 2DEG Sheet Density p. 142
- 3.4.3 2DEG Mobility p. 154
- 3.4.4 Spontaneous and Piezoelectric Polarization Effects p. 157
- References p. 160
- 4 MESFETs p. 163
- 4.1 Introduction p. 163
- 4.2 DC Analysis p. 166
- 4.2.1 The PHS Model p. 167
- 4.2.2 The Cappy Model p. 176
- 4.3 Small-Signal Analysis p. 180
- 4.3.1 Small-Signal Equivalent Circuit p. 180
- 4.3.2 Modeling the Equivalent Circuit Elements Based on the PHS Model p. 184
- 4.3.3 Modeling the Equivalent Circuit Elements Based on the Cappy Model p. 187
- 4.3.4 Small-Signal Parameters and Gains p. 189
- 4.4 Noise Analysis p. 194
- 4.4.1 Noise Mechanisms p. 194
- 4.4.2 Noise Modeling Using the PHS Noise Model p. 197
- 4.4.3 Noise Modeling Using the Cappy Noise Model p. 199
- 4.4.4 Minimum Noise Figure p. 199
- 4.5 Power Analysis p. 204
- 4.6 Issues of GaAs MESFETs p. 208
- 4.6.1 Transistor Structures p. 208
- 4.6.2 Low-Noise GaAs MESFETs p. 210
- 4.6.3 Power GaAs MESFETs p. 216
- 4.7 Issues of Wide Bandgap MESFETs p. 222
- 4.7.1 Transistor Structures p. 222
- 4.7.2 SiC MESFETs p. 223
- 4.7.3 GaN MESFETs p. 225
- References p. 226
- 5 High Electron Mobility Transistors p. 231
- 5.1 Introduction p. 231
- 5.2 DC Analysis p. 237
- 5.2.1 PHS-Like HEMT Model p. 237
- 5.2.2 Cappy-Like HEMT Model p. 246
- 5.3 Small-Signal Analysis p. 253
- 5.3.1 Introduction p. 253
- 5.3.2 Modeling the Circuit Elements Based on the PHS-Like Model p. 254
- 5.3.3 Modeling the Circuit Elements Based on the Cappy-Like Model p. 259
- 5.3.4 The Concept of Modulation Efficiency p. 259
- 5.3.5 The Concept of Delay Times p. 262

- 5.4 Noise and Power Analysis p. 265
- 5.5 Issues of AlGaAs/GaAs HEMTs p. 266
 - 5.5.1 Transistor Structures p. 266
 - 5.5.2 Low-Noise AlGaAs/GaAs HEMTs p. 267
 - 5.5.3 Power AlGaAs/GaAs HEMTs p. 267
- 5.6 Issues of GaAs pHEMTs p. 270
 - 5.6.1 Transistor Structures p. 270
 - 5.6.2 Low-Noise GaAs pHEMTs p. 271
 - 5.6.3 Power GaAs pHEMTs p. 273
- 5.7 Issues of GaAs mHEMTs p. 273
 - 5.7.1 Transistor Structures p. 273
 - 5.7.2 Performance of GaAs mHEMTs p. 275
- 5.8 Issues of InP HEMTs p. 276
 - 5.8.1 Transistor Structures p. 276
 - 5.8.2 Low-Noise InP HEMTs p. 278
 - 5.8.3 Power InP HEMTs p. 280
- 5.9 Issues of AlGaN/GaN HEMTs p. 280
 - 5.9.1 Transistor Structures p. 280
 - 5.9.2 AlGaN/GaN HEMT Performance p. 282
- References p. 284
- 6 MOSFETs p. 292
 - 6.1 Introduction p. 292
 - 6.2 Two-Terminal MOS Structure p. 295
 - 6.2.1 Qualitative Description p. 295
 - 6.2.2 Derivation of the Threshold Voltage p. 299
 - 6.3 DC Analysis p. 302
 - 6.3.1 Introduction p. 302
 - 6.3.2 PHS-Like MOSFET Model p. 303
 - 6.3.3 Effective Mobility p. 307
 - 6.3.4 Modifications of the Threshold Voltage p. 310
 - 6.4 Small-Signal Analysis p. 313
 - 6.4.1 MESFET/HEMT-Like Equivalent Circuit p. 313
 - 6.4.2 Transmission Line Model p. 316
 - 6.4.3 Compact Models p. 319
 - 6.5 Noise and Power Analysis p. 320
 - 6.6 Issues of Small-Signal Low-Noise MOSFETs p. 321
 - 6.6.1 Transistor Structures p. 321
 - 6.6.2 Si MOSFET Performance p. 322
 - 6.7 Issues of Power MOSFETs p. 324
 - References p. 327
- 7 Silicon Bipolar Junction Transistors p. 334
 - 7.1 Introduction p. 334
 - 7.2 DC Analysis p. 344
 - 7.2.1 First-Order Model Development p. 344
 - 7.2.2 Extensions of the First-Order Model p. 348
 - 7.3 Small-Signal Analysis p. 371

- 7.3.1 Small-Signal Equivalent Circuit p. 371
- 7.3.2 Delay Time Analysis p. 376
- 7.3.3 Cutoff Frequency and Maximum Frequency of Oscillation p. 378
- 7.4 Noise Analysis p. 379
- 7.5 Power Analysis p. 384
- 7.6 Issues of Si BJTs p. 387
 - 7.6.1 Transistor Structures p. 387
 - 7.6.2 BJT Performance p. 390
 - 7.6.3 Low-Noise BJTs p. 394
 - 7.6.4 Power BJTs p. 395
- References p. 397
- 8 Heterojunction Bipolar Transistors p. 400
 - 8.1 Introduction p. 400
 - 8.2 DC Analysis p. 405
 - 8.2.1 Minority Carrier and Bandgap Narrowing Parameters p. 405
 - 8.2.2 HBTs with Smooth Emitter-Base Heterojunction p. 408
 - 8.2.3 HBTs with Spike Emitter-Base Heterojunction p. 413
 - 8.2.4 HBT Structures with a Reduced Spike p. 415
 - 8.2.5 Other Issues Related to HBT DC Behavior p. 417
 - 8.3 Small-Signal, Noise, and Power Analysis of HBTs p. 422
 - 8.4 Self-Heating of HBTs p. 424
 - 8.4.1 Temperature-Dependent Collector Current in Multifinger HBTs p. 424
 - 8.4.2 Temperature Dependence of Current Gain p. 427
 - 8.4.3 Current Gain Collapse p. 430
 - 8.5 Issues of GaAs-Based HBTs p. 432
 - 8.5.1 Transistor Structures p. 432
 - 8.5.2 GaAs-Based HBT Performance p. 440
 - 8.6 Issues of InP-Based HBTs p. 443
 - 8.6.1 Transistor Structures p. 443
 - 8.6.2 InP HBT Performance p. 448
 - 8.7 Issues of SiGe HBTs p. 450
 - 8.7.1 Transistor Structures p. 450
 - 8.7.2 SiGe HBT Performance p. 457
- References p. 461
- Appendixes
 - A.1 Frequently Used Symbols p. 469
 - A.2 Physical Constants and Unit Conversions p. 473
 - A.3 Microwave Frequency Bands p. 476
 - A.4 Two-Port Calculations p. 477
 - A.5 Important Material Properties of Selected Materials p. 481
- Index p. 483